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Correction: All-solution-processed, flexible thin-film transistor based on PANI/PETA as gate/gate insulator

 Jin-Yong Hong,^{†a} Kyoung-Hwan Shin,^{†b} Dai Gun Yoon,^{*c} Byung Doo Chin^{*c}
and Sung Hyun Kim^{*d}

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 Correction for 'All-solution-processed, flexible thin-film transistor based on PANI/PETA as gate/gate insulator' by Jin-Yong Hong *et al.*, *RSC Adv.*, 2015, 5, 105785–105788.

The authors regret the omission of one of the authors, Kyoung-Hwan Shin, from the original manuscript. The corrected author list is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aDepartment of Electrical Engineering and Computer Science, Massachusetts Institute of Technology, 77 Massachusetts Avenue, Cambridge, MA 02139, USA

^bSchool of Chemical and Biological Engineering, Seoul National University, Seoul 151-747, Republic of Korea

^cDepartment of Polymer Science and Engineering, Dankook University, Youngin 448-701, Republic of Korea. E-mail: bdchin@dankook.ac.kr

^dDepartment of Chemistry, College of Natural Sciences, Seoul National University, Seoul 151-747, Republic of Korea. E-mail: shkim75@snu.ac.kr

† These authors contributed equally to this work.

